ABSTRACT

A semiconductor device includes a lower pattern on a substrate, a source/drain pattern including a semiconductor liner film in contact with the lower pattern, and an epitaxial insulating liner extending along at least a portion of a sidewall of the semiconductor liner film and in contact with the semiconductor liner film, wherein the semiconductor liner film includes a first portion including a first point spaced apart from the lower pattern at a first height and a second point spaced apart from the lower pattern at a second height greater than the first height, a width of the semiconductor liner film in a second direction at the first point is less than a width of the semiconductor liner film in the second direction at the second point, and the epitaxial insulating liner extends along at least a portion of a sidewall of the first portion of the semiconductor liner film.

FIG. 4